

A cross-sectional view of a semiconductor device. A central structure 10 is positioned on a substrate 11. The structure 10 includes a top layer 12, a middle layer 14, and a bottom layer 16. The bottom layer 16 is shown with a cross-hatched pattern. The structure 10 is flanked by two side regions 18, which are shown with a diagonal hatched pattern. The side regions 18 are separated by a central gap 20. The substrate 11 is shown with a bottom layer 15 and a top layer 18A. The top layer 18A is shown with a diagonal hatched pattern. The central gap 20 is defined by two vertical lines 22.

(Prior Art)

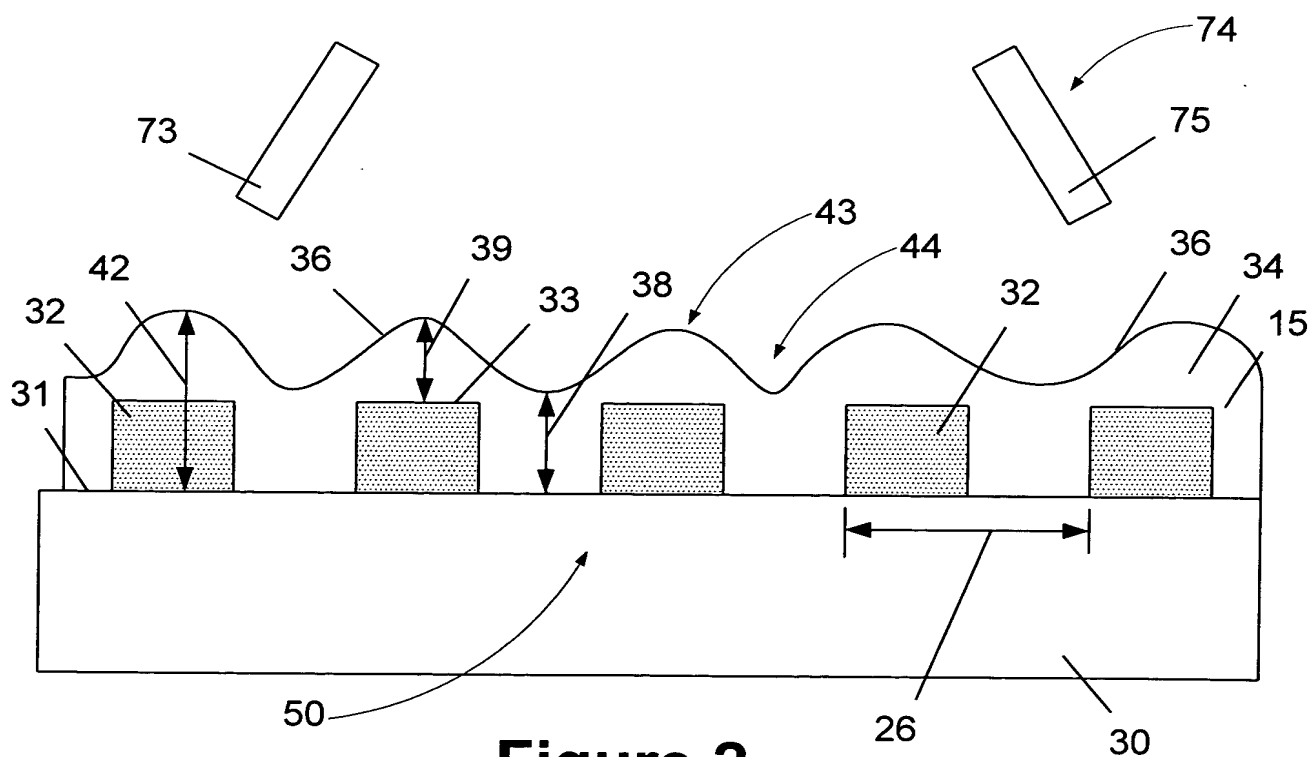


Figure 2

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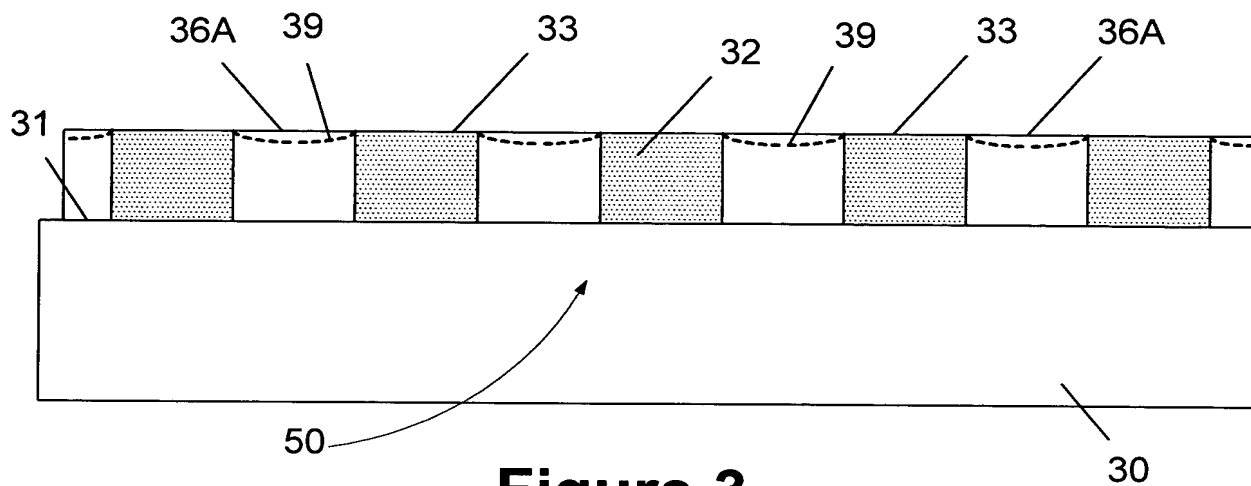


Figure 3

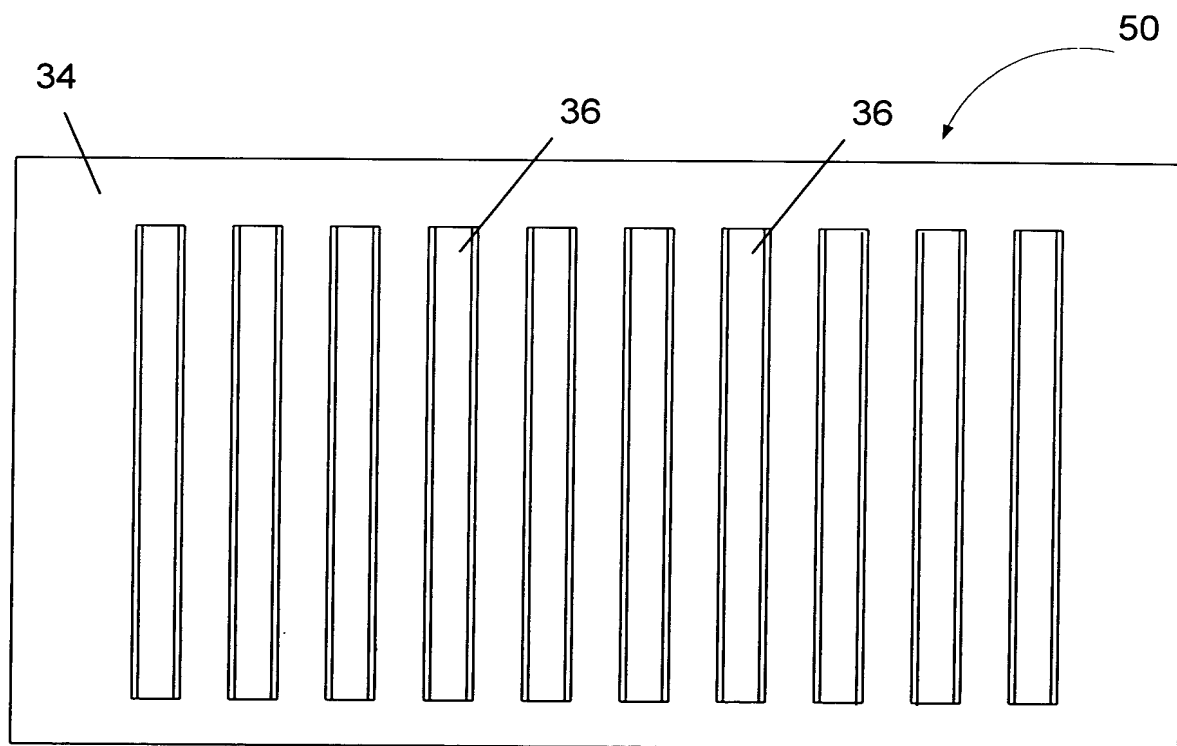


Figure 4

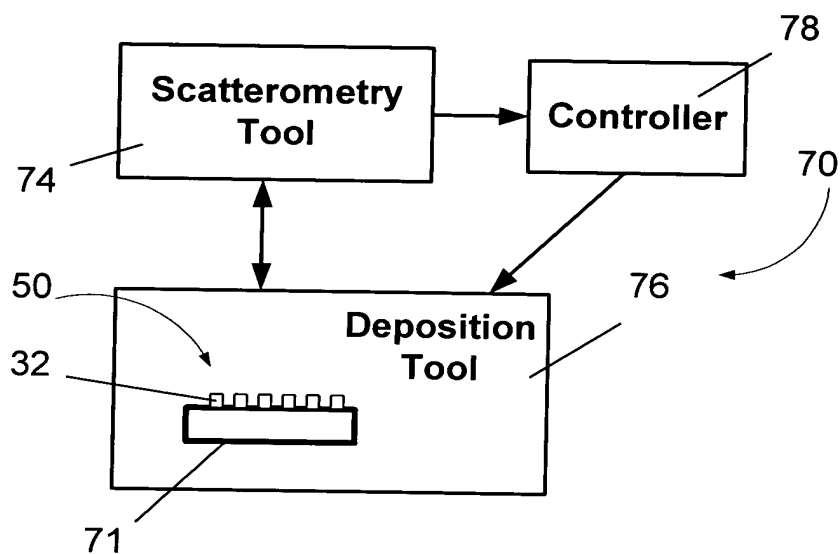


Figure 5